

# UNISONIC TECHNOLOGIES CO., LTD

2N7002Z **Preliminary Power MOSFET** 

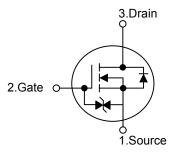
## INTERFACE AND SWITCHING (300mA, 60Volts)

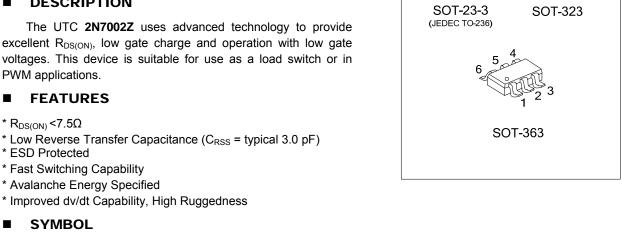
#### **DESCRIPTION**

excellent R<sub>DS(ON)</sub>, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

- \*  $R_{DS(ON)}$  < 7.5 $\Omega$
- \* ESD Protected

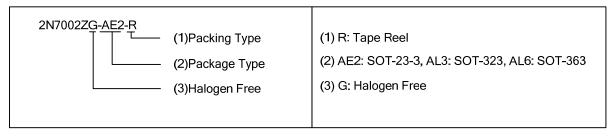






#### **ORDERING INFORMATION**

Ordering Number	Dookogo	Pin Assignment						Dooking	
	Ordering Number	Package	1	2	3	4	5	6	Packing
	2N7002ZG-AE2-R	SOT-23-3	S	G	D	-	-	-	Tape Reel
	2N7002ZG-AL3-R	SOT-323	S	G	D	-	-	-	Tape Reel
	2N7002ZG-AL6-R	SOT-363	S1	G1	D2	S2	G2	D1	Tape Reel



#### **MARKING**



### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)

PARAMET	ER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		$V_{DSS}$	60	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Drain Current	Continuous	ı	300	mA	
Diam Current	Pulse(Note 2)	I <sub>D</sub>	800	] IIIA	
Power Dissipation	ower Dissipation		225	mW	
Junction Temperature		$T_J$	+150	°C	
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C	

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

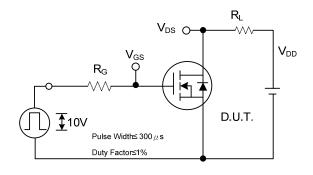
#### ■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =10 $\mu$ A	60			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1.0	μΑ
Gate-Source Leakage Current	$I_{GSS}$	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±10	μΑ
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.0	1.85	2.5	V
Static Drain-Source On-Resistance (Note)	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A			7.5	0
Static Dialii-Source Oil-Resistance (Note)		$V_{GS}$ =5V, $I_{D}$ =0.05A			7.5	12
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V, I <sub>D</sub> =0.2A	80			mS
DYNAMIC PARAMETERS	_		-		-	_
Input Capacitance	C <sub>ISS</sub>			25	50	pF
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, f=1.0MHz		10	25	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			3.0	5.0	pF
SWITCHING PARAMETERS	_		-		-	_
Turn-ON Delay Time	t <sub>D(ON)</sub>	$I_D$ =0.2 A, $V_{DD}$ =30V, $V_{GS}$ =10V,		12	20	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$R_L=150\Omega$ , $R_G=10\Omega$		20	30	ns
DRAIN-SOURCE DIODE CHARACTERIST	ICS AND MA	XIMUM RATINGS				
Drain-Source Diode Forward Voltage	$V_{SD}$	V <sub>GS</sub> =0V, Is=115mA (Note )		0.88	1.5	V
Maximum Pulsed Drain-Source Diode					0.8	Α
Forward Current	I <sub>SM</sub>				0.0	A
Maximum Continuous Drain-Source Diode	ls				115	mA
Forward Current	10				113	шл

Note: Pulse width ≤ 300 µs, Duty cycle ≤ 1%

<sup>2.</sup> Pulse width  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

#### TEST CIRCUITS AND WAVEFORMS



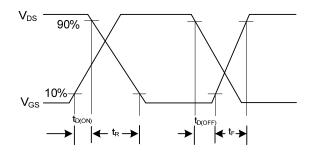


Fig. 2A Switching Test Circuit

Fig. 2B Switching Waveforms

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